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Docket Number (Optional) PRM-0052	Application Number 10/550,643				
Applicant(s) Kunihiko Iwamoto et al.					
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IC14 Rec'd PUI/PIU ZO SEP LUUS ATTY DOCKET NO. PRM-0052 INFORMATION DISCLOSURE CITATION Kunihiko Iwamoto et al. (Use several sheets if necessary) **GROUP ART** FILING 292G **U.S. PATENT DOCUMENTS** FILING DATE **EXAMINER** CLASS SUBCLASS DATE NAME DOCUMENT NUMBER IF APPROPRIATE INITIAL U.S. PATENT APPLICATION PUBLICATIONS FILING DATE EXAMINER CLASS SUBCLASS DOCUMENT NUMBER DATE NAME IF APPROPRIATE INITIAL **FOREIGN PATENT DOCUMENTS TRANSLATION** COUNTRY CLASS SUBCLASS DATE DOCUMENT NUMBER YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Hyung-Seok Jung et al. "Improved Current Performance of CMOSFETs with Nitrogen Incorporated HfO2-Al2O3 Laminate Gate Dielectric", Electron Devices Meeting, 2002. IEDM' 02.Digest. International, 2002, 12, pages 853-856. /ER/ T. Nishimura et al. "Effects of Nitrogen Incorporation into HfA1Ox Films on Gate Leakage Current - From XPS Study of Hf Bonding States", Extended Abstracts of International Workshop On Gate Insulator 2003, 11, pages 180-185. /ER/ DATE CONSIDERED 06/25/2007 **EXAMINER** /Eduardo Rodela/ *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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